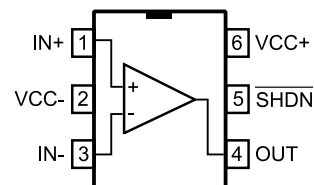


## Description

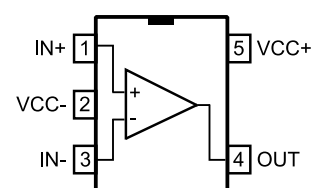
The TSV6390, TSV6391, and their "A" versions are single operational amplifiers (op amps) offering low voltage, low power operation, and rail-to-rail input and output.

With a very low input bias current and low offset voltage (500  $\mu$ V maximum for the A version), the TSV6390 and TSV6391 are ideal for applications requiring precision. The devices can operate at power supplies ranging from 1.5 to 5.5 V, and are therefore ideal for battery-powered devices, extending battery life.

When used with a gain (above -3 or 4), these products feature an excellent speed/power consumption ratio, offering a 2.4 MHz gain bandwidth product while consuming only 60  $\mu$ A at a 5 V supply voltage.



TSV6390ICT/ILT  
SC70-6/SOT23-6



TSV6391ICT/ILT  
SC70-5/SOT23-5

## Features

- Low offset voltage: 500  $\mu$ V max (A version)
- Low power consumption: 60  $\mu$ A typ at 5 V
- Low supply voltage: 1.5 V – 5.5 V
- Gain bandwidth product: 2.4 MHz typical
- Stable in gain configuration (-3 or 4)
- Low power shutdown mode: 5 nA typical
- High output current: 63 mA at  $V_{CC} = 5$  V
- Low input bias current: 1 pA typical
- Rail-to-rail input and output
- Extended temperature range:  
-40  $^{\circ}$ C to 125  $^{\circ}$ C
- 4 kV human body model

## Applications

- Battery-powered applications
- Portable devices
- Signal conditioning
- Active filtering
- Medical instrumentation

## Absolute maximum ratings and operating conditions

**Table 1: Absolute maximum ratings (AMR)**

Symbol	Parameter	Value	Unit	
$V_{CC}$	Supply voltage <sup>(1)</sup>	6	V	
$V_{id}$	Differential input voltage <sup>(2)</sup>	$\pm V_{CC}$		
$V_{in}$	Input voltage <sup>(3)</sup>	$(V_{CC-}) - 0.2$ to $(V_{CC+}) + 0.2$		
$I_{in}$	Input current <sup>(4)</sup>	10	mA	
$\overline{SHDN}$	Shutdown voltage <sup>(3)</sup>	$(V_{CC-}) - 0.2$ to $(V_{CC+}) + 0.2$	V	
$T_{stg}$	Storage temperature	-65 to 150	°C	
$T_j$	Maximum junction temperature	150		
$R_{thja}$	Thermal resistance junction to ambient <sup>(5)(6)</sup>	SC70-6	232	°C/W
		SOT23-6	240	
		SC70-5	205	
		SOT23-5	250	
ESD	HBM: human body model <sup>(7)</sup>	4	kV	
	MM: machine model <sup>(8)</sup>	300	V	
	CDM: charged device model <sup>(9)</sup>	1.5	kV	
	Latch-up immunity	200	mA	

**Notes:**

- <sup>(1)</sup> All voltage values, except the differential voltage, are with respect to network ground terminal.
- <sup>(2)</sup> The differential voltage is the non-inverting input terminal with respect to the inverting input terminal.
- <sup>(3)</sup>  $V_{CC-} - V_{in}$  must not exceed 6 V,  $V_{in}$  must not exceed 6 V.
- <sup>(4)</sup> Input current must be limited by a resistor in series with the inputs.
- <sup>(5)</sup>  $R_{th}$  are typical values.
- <sup>(6)</sup> Short-circuits can cause excessive heating and destructive dissipation.
- <sup>(7)</sup> Human body model: 100 pF discharged through a 1.5 k $\Omega$  resistor between two pins of the device, done for all couples of pin combinations with other pins floating.
- <sup>(8)</sup> Machine model: a 200 pF capacitor is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5  $\Omega$ ), done for all couples of pin combinations with other pins floating.
- <sup>(9)</sup> Charged device model: all pins plus package are charged together to the specified voltage and then discharged directly to the ground.

**Table 2: Operating conditions**

Symbol	Parameter	Value	Unit
$V_{CC}$	Supply voltage	1.5 to 5.5	V
$V_{icm}$	Common mode input voltage range	$(V_{CC-}) - 0.1$ to $(V_{CC+}) + 0.1$	
$T_{oper}$	Operating free air temperature range	-40 to 125	°C

## Electrical characteristics

**Table 3: Electrical characteristics at VCC+ = 1.8 V with VCC- = 0 V, Vicm = VCC/2, Tamb = 25 °C and RL connected to VCC/2 (unless otherwise specified)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>DC performance</b>						
V <sub>io</sub>	Offset voltage	TSV6390 and TSV6391			3	mV
		TSV6390A and TSV6391A			0.5	
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub> , TSV6390 and TSV6391			4.5	
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub> , TSV6390A and TSV6391A			2	
$\Delta V_{io}/\Delta T$	Input offset voltage drift			2		$\mu$ V/°C
I <sub>io</sub>	Input offset current, V <sub>out</sub> = V <sub>CC</sub> /2 <sup>(1)</sup>			1	10	pA
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>		1	100	
I <sub>ib</sub>	Input bias current, (V <sub>out</sub> = V <sub>CC</sub> /2) <sup>(1)</sup>			1	10	pA
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>		1	100	
CMR	Common mode rejection ratio 20 log ( $\Delta V_{io}/\Delta V_{io}$ )	0 V to 1.8 V, V <sub>out</sub> = 0.9 V	53	74		dB
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	51			
A <sub>vd</sub>	Large signal voltage gain	R <sub>L</sub> = 10 k $\Omega$ , V <sub>out</sub> = 0.5 V to 1.3 V	85	95		dB
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	80			
V <sub>OH</sub>	High-level output voltage	R <sub>L</sub> = 10 k $\Omega$		5	35	mV
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>			50	
V <sub>OL</sub>	Low-level output voltage	R <sub>L</sub> = 10 k $\Omega$		4	35	mV
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>			50	
I <sub>out</sub>	I <sub>sink</sub>	V <sub>out</sub> = 1.8 V	6	12		mA
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	4			
	I <sub>source</sub>	V <sub>out</sub> = 0 V	6	10		
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	4			
I <sub>CC</sub>	Supply current, $\overline{\text{SHDN}} = V_{CC}$	No load, V <sub>out</sub> = V <sub>CC</sub> /2	40	50	60	$\mu$ A
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>			62	
<b>AC performance</b>						
GBP	Gain bandwidth product	R <sub>L</sub> = 10 k $\Omega$ , C <sub>L</sub> = 100 pF		2		MHz
Gain	Minimum gain for stability	Phase margin = 60°, R <sub>f</sub> = 10 k $\Omega$ , R <sub>L</sub> = 10 k $\Omega$ , C <sub>L</sub> = 20 pF		4		V/V
				-3		
SR	Slew rate	R <sub>L</sub> = 10 k $\Omega$ , C <sub>L</sub> = 100 pF, V <sub>out</sub> = 0.5 V to 1.3 V		0.7		V/ $\mu$ s
e <sub>n</sub>	Equivalent input noise voltage	f = 1 kHz		60		nV/ $\sqrt$ Hz
		f = 10 kHz		33		

**Table 4: Shutdown characteristics VCC = 1.8 V (TSV6390)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>DC performance</b>						
$I_{CC}$	Supply current in shutdown mode (all operators)	$\overline{SHDN} = V_{CC-}$		2.5	50	nA
		$T_{min} < T_{op} < 85\text{ }^{\circ}\text{C}$			200	
		$T_{min} < T_{op} < 125\text{ }^{\circ}\text{C}$				1.5
$t_{on}$	Amplifier turn-on time	$R_L = 2\text{ k}\Omega$ , $V_{out} = (V_{CC-})$ to $(V_{CC-}) + 0.2\text{ V}$		300		ns
$t_{off}$	Amplifier turn-off time	$R_L = 2\text{ k}\Omega$ , $V_{out} = (V_{CC+}) - 0.5\text{ V}$ to $(V_{CC+}) - 0.7\text{ V}$		20		
$V_{IH}$	$\overline{SHDN}$ logic high		1.3			V
$V_{IL}$	$\overline{SHDN}$ logic low				0.5	
$I_{IH}$	$\overline{SHDN}$ current high	$\overline{SHDN} = V_{CC+}$		10		pA
$I_{IL}$	$\overline{SHDN}$ current low	$\overline{SHDN} = V_{CC-}$		10		
$I_{OLeak}$	Output leakage in shutdown mode	$\overline{SHDN} = V_{CC-}$		50		
		$T_{min} < T_{op} < T_{max}$		1		nA

## Micropower (60 $\mu$ A), wide bandwidth (2.4 MHz) CMOS operational amplifiers

**Table 5: VCC+ = 3.3 V, VCC- = 0 V, Vicm = VCC/2, Tamb = 25 °C, RL connected to VCC/2 (unless otherwise specified)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>DC performance</b>						
V <sub>io</sub>	Offset voltage	TSV6390 and TSV6391			3	mV
		TSV6390A and TSV6391A			0.5	
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub> , TSV6390 and TSV6391			4.5	
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub> , TSV6390A and TSV6391A			2	
$\Delta V_{io}/\Delta T$	Input offset voltage drift			2		$\mu$ V/°C
I <sub>io</sub>	Input offset current <sup>(1)</sup>			1	10	pA
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>		1	100	
I <sub>ib</sub>	Input bias current <sup>(1)</sup>			1	10	pA
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>		1	100	
CMR	Common mode rejection ratio 20 log ( $\Delta V_{ic}/\Delta V_{io}$ )	0 V to 3.3 V, V <sub>out</sub> = 1.65 V	57	79		dB
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	53			
A <sub>vd</sub>	Large signal voltage gain	R <sub>L</sub> = 10 k $\Omega$ , V <sub>out</sub> = 0.5 V to 2.8 V	88	98		dB
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	83			
V <sub>OH</sub>	High-level output voltage	R <sub>L</sub> = 10 k $\Omega$		6	35	mV
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>			50	
V <sub>OL</sub>	Low-level output voltage	R <sub>L</sub> = 10 k $\Omega$		7	35	mV
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>			50	
I <sub>out</sub>	I <sub>sink</sub>	V <sub>out</sub> = 3.3 V	23	45		mA
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	20	42		
	I <sub>source</sub>	V <sub>out</sub> = 0 V	23	38		
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	20			
I <sub>CC</sub>	Supply current, $\overline{\text{SHDN}} = V_{CC}$	No load, V <sub>out</sub> = V <sub>CC</sub> /2	43	55	64	$\mu$ A
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>			66	
<b>AC performance</b>						
GBP	Gain bandwidth product	R <sub>L</sub> = 10 k $\Omega$ , C <sub>L</sub> = 100 pF		2.2		MHz
Gain	Minimum gain for stability	Phase margin = 60°, R <sub>f</sub> = 10 k $\Omega$ , R <sub>L</sub> = 10 k $\Omega$ , C <sub>L</sub> = 20 pF,		4		V/V
				-3		
SR	Slew rate	R <sub>L</sub> = 10 k $\Omega$ , C <sub>L</sub> = 100 pF, V <sub>out</sub> = 0.5 V to 2.8 V		0.9		V/ $\mu$ s
e <sub>n</sub>	Equivalent input noise voltage	f = 1 kHz		65		nV/ $\sqrt{\text{Hz}}$

## Micropower (60 $\mu$ A), wide bandwidth (2.4 MHz) CMOS operational amplifiers

**Table 6: Electrical characteristics at VCC+ = 5 V with VCC- = 0 V, Vicm = VCC/2, Tamb = 25 °C and RL connected to VCC/2 (unless otherwise specified)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>DC performance</b>						
V <sub>io</sub>	Offset voltage	TSV6390 and TSV6391			3	mV
		TSV6390A and TSV6391A			0.5	
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub> , TSV6390 and TSV6391			4.5	
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub> , TSV6390A and TSV6391A			2	
$\Delta V_{io}/\Delta T$	Input offset voltage drift			2		$\mu$ V/°C
I <sub>io</sub>	Input offset current, V <sub>out</sub> = V <sub>CC</sub> /2 <sup>(1)</sup>			1	10	pA
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>		1	100	
I <sub>ib</sub>	Input bias current, V <sub>out</sub> = V <sub>CC</sub> /2 <sup>(1)</sup>			1	10	pA
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>		1	100	
CMR	Common mode rejection ratio 20 log ( $\Delta V_{io}/\Delta V_{io}$ )	0 V to 5 V, V <sub>out</sub> = 2.5 V	60	80		dB
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	55			
SVR	Supply voltage rejection ratio 20 log ( $\Delta V_{CC}/\Delta V_{io}$ )	V <sub>CC</sub> = 1.8 to 5 V	75	93		dB
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	73			
A <sub>vd</sub>	Large signal voltage gain	R <sub>L</sub> = 10 k $\Omega$ , V <sub>out</sub> = 0.5 V to 4.5 V	89	98		
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	84			
V <sub>OH</sub>	High-level output voltage	R <sub>L</sub> = 10 k $\Omega$		7	35	mV
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>			50	
V <sub>OL</sub>	Low-level output voltage	R <sub>L</sub> = 10 k $\Omega$		6	35	mV
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>			50	
I <sub>out</sub>	I <sub>sink</sub>	V <sub>out</sub> = 5 V	40	65		mA
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	35			
	I <sub>source</sub>	V <sub>out</sub> = 0 V	40	72		
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>	35			
I <sub>CC</sub>	Supply current, $\overline{\text{SHDN}} = V_{CC}$	No load, V <sub>out</sub> = V <sub>CC</sub> /2	50	60	69	$\mu$ A
		T <sub>min</sub> < T <sub>op</sub> < T <sub>max</sub>			72	
<b>AC performance</b>						
GBP	Gain bandwidth product	R <sub>L</sub> = 10 k $\Omega$ , C <sub>L</sub> = 100 pF		2.4		MHz
Gain	Minimum gain for stability	Phase margin = 60°, R <sub>f</sub> = 10 k $\Omega$ , R <sub>L</sub> = 10 k $\Omega$ , C <sub>L</sub> = 20 pF,		4		V/V
				-3		
SR	Slew rate	R <sub>L</sub> = 10 k $\Omega$ , C <sub>L</sub> = 100 pF		1.1		V/ $\mu$ s
e <sub>n</sub>	Equivalent input noise voltage	f = 1 kHz		60		nV/ $\sqrt$ Hz
		f = 10 kHz		33		
THD+N	Total harmonic distortion + noise	A <sub>v</sub> = -10, f <sub>in</sub> = 1 kHz, R = 100 k $\Omega$ , V <sub>icm</sub> = V <sub>CC</sub> /2, V <sub>in</sub> = 40 mVpp		0.11		%

**Table 7: Shutdown characteristics VCC = 5 V (TSV6390)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>DC performance</b>						
$I_{CC}$	Supply current in shutdown mode (all operators)	$\overline{\text{SHDN}} = V_{CC-}$		5	50	nA
		$T_{\min} < T_{op} < 85\text{ }^{\circ}\text{C}$			200	
		$T_{\min} < T_{op} < 125\text{ }^{\circ}\text{C}$				1.5
$t_{on}$	Amplifier turn-on time	$R_L = 2\text{ k}\Omega, V_{out} = (V_{CC-}) \text{ to } (V_{CC-}) + 0.2\text{ V}$		300		ns
$t_{off}$	Amplifier turn-off time	$R_L = 2\text{ k}\Omega, V_{out} = (V_{CC+}) - 0.5\text{ V to } (V_{CC+}) - 0.7\text{ V}$		30		
$V_{IH}$	$\overline{\text{SHDN}}$ logic high		4.5			V
$V_{IL}$	$\overline{\text{SHDN}}$ logic low				0.5	
$I_{IH}$	$\overline{\text{SHDN}}$ current high	$\overline{\text{SHDN}} = V_{CC+}$		10		$\mu\text{A}$
$I_{IL}$	$\overline{\text{SHDN}}$ current low	$\overline{\text{SHDN}} = V_{CC-}$		10		
$I_{OLeak}$	Output leakage in shutdown mode	$\overline{\text{SHDN}} = V_{CC-}$		50		
		$T_{\min} < T_{op} < T_{\max}$		1		nA

**Electrical characteristics curves**

Figure 1: Supply current vs. supply voltage at  $V_{icm} = V_{CC}/2$

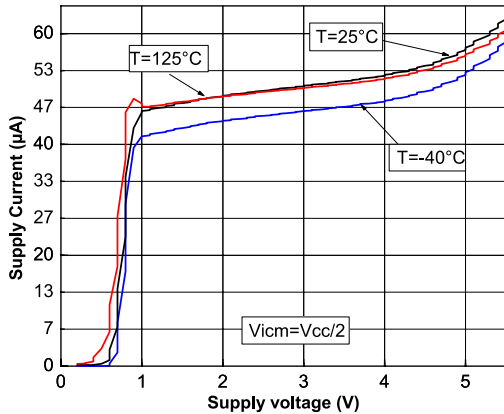


Figure 2: Output current vs. output voltage at  $V_{CC} = 1.5$  V

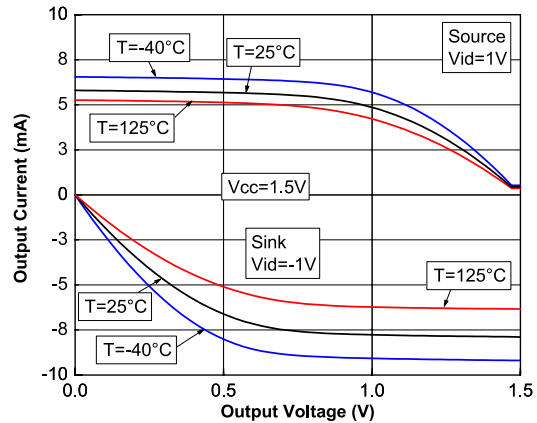


Figure 3: Output current vs. output voltage at  $V_{CC} = 5$  V

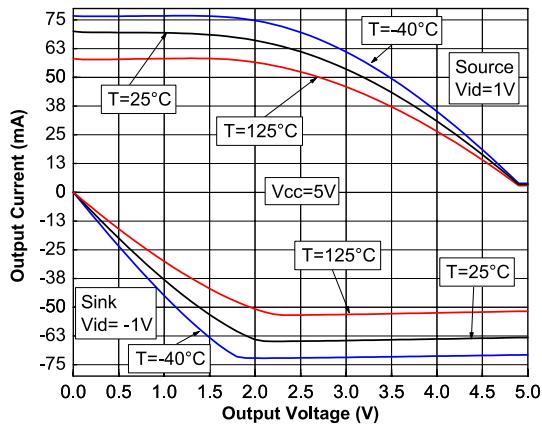


Figure 4: Peaking at closed loop gain = -10

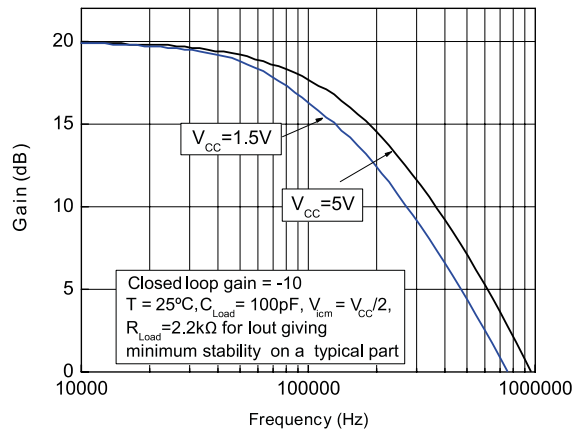


Figure 5: Peaking at closed loop gain = -3 at  $V_{CC} = 1.5$  V

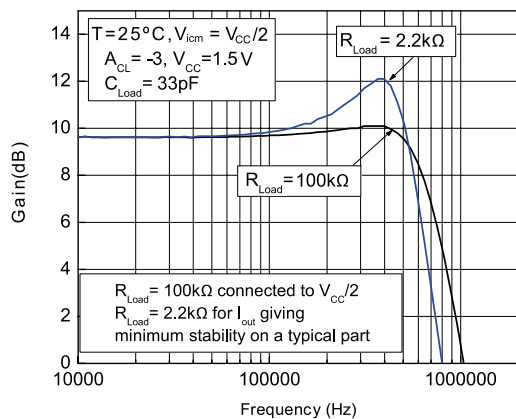


Figure 6: Peaking at closed loop gain = -3 at  $V_{CC} = 5$  V

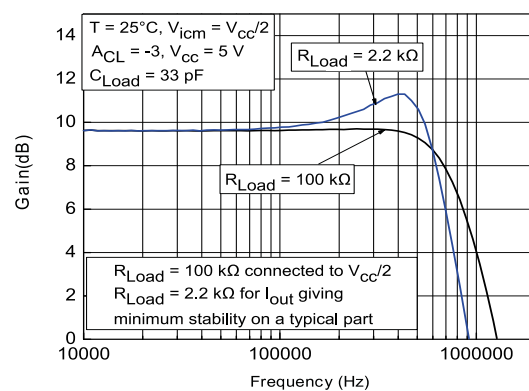




Figure 7: Positive slew rate vs. supply voltage

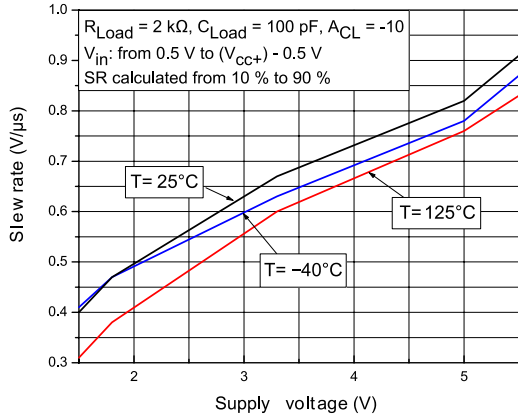


Figure 8: Negative slew rate vs. supply voltage

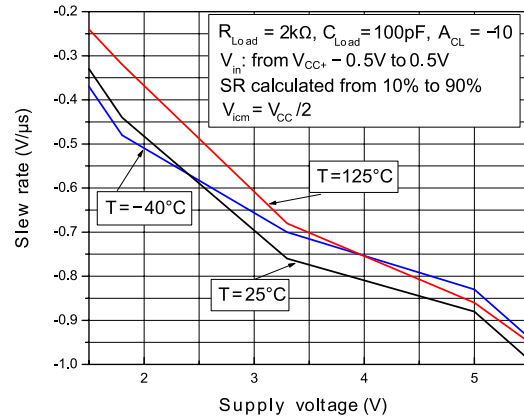


Figure 9: Distortion + noise vs. output voltage at VCC = 1.8 V

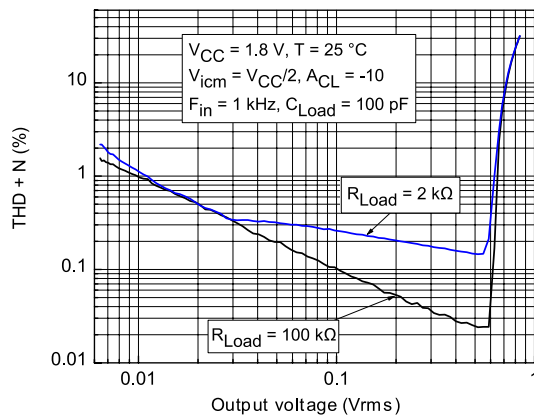


Figure 10: Distortion + noise vs. output voltage at VCC = 5 V

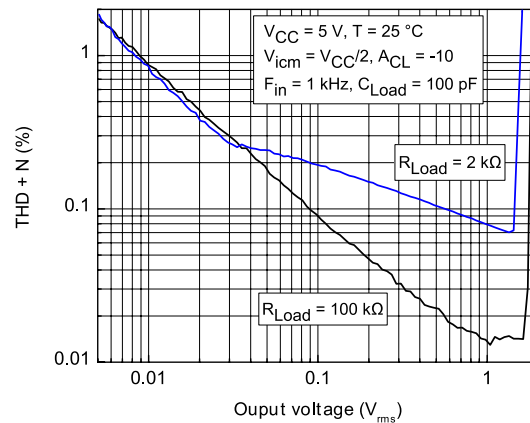


Figure 11: Slew rate timing

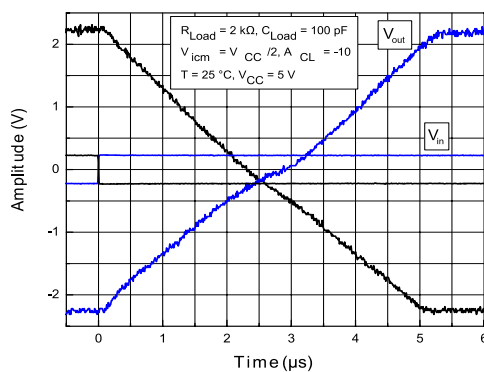


Figure 12: Noise vs. frequency at VCC = 5 V

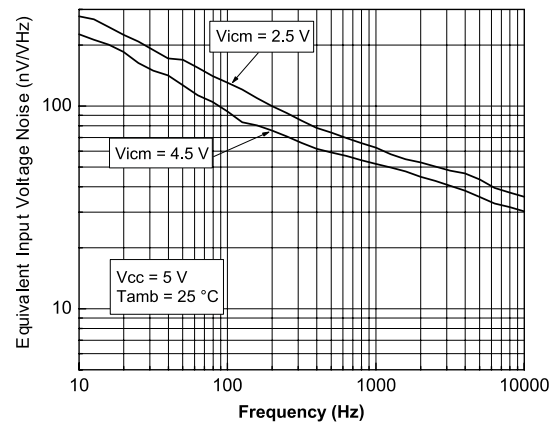


Figure 13: Input offset voltage vs input common-mode at  $V_{CC} = 1.5$  V

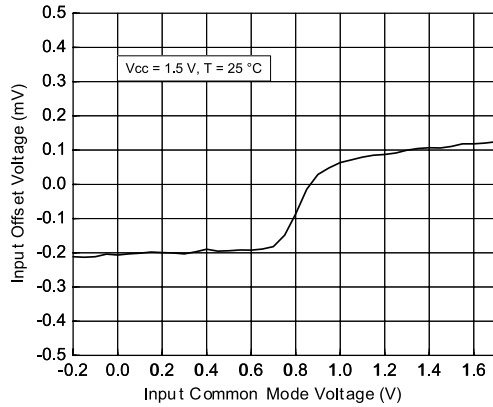


Figure 14: Input offset voltage vs input common-mode at  $V_{CC} = 5$  V

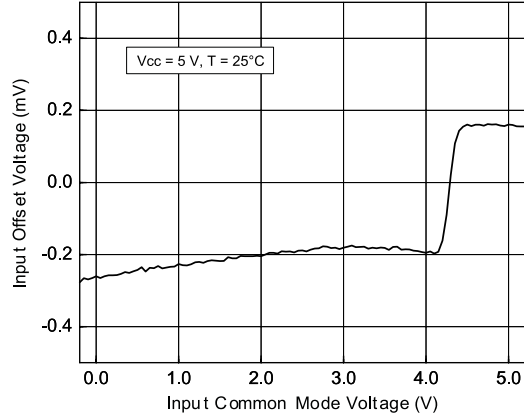


Figure 15: Test configuration for turn-on time ( $V_{out}$  pulled down)

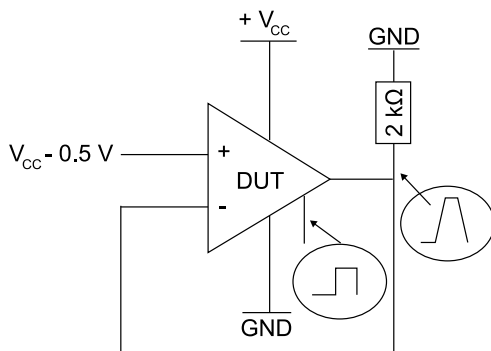


Figure 16: Test configuration for turn-off time ( $V_{out}$  pulled down)

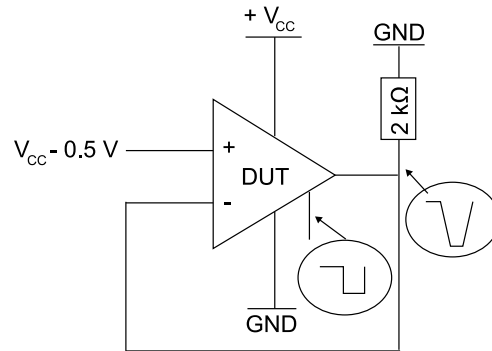


Figure 17: Turn-on time,  $V_{CC} = 5$  V,  $V_{out}$  pulled down,  $T = 25$  °C

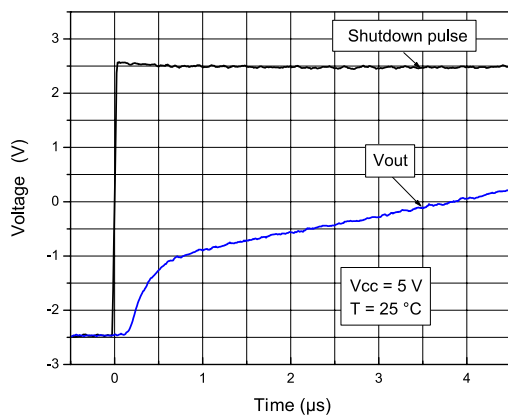
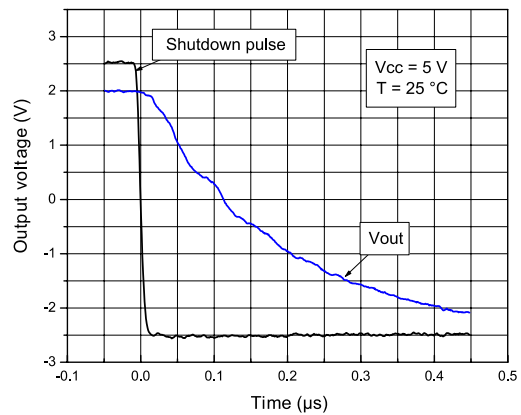
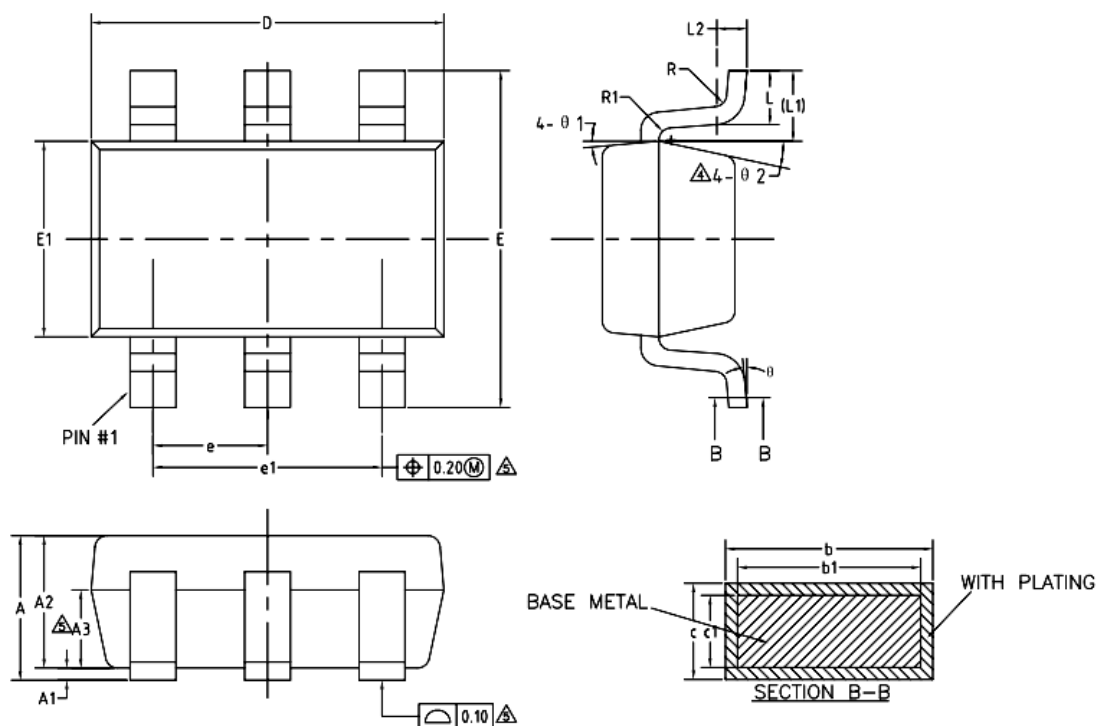


Figure 18: Turn-off time,  $V_{CC} = 5$  V,  $V_{out}$  pulled down,  $T = 25$  °C



Package Dimension

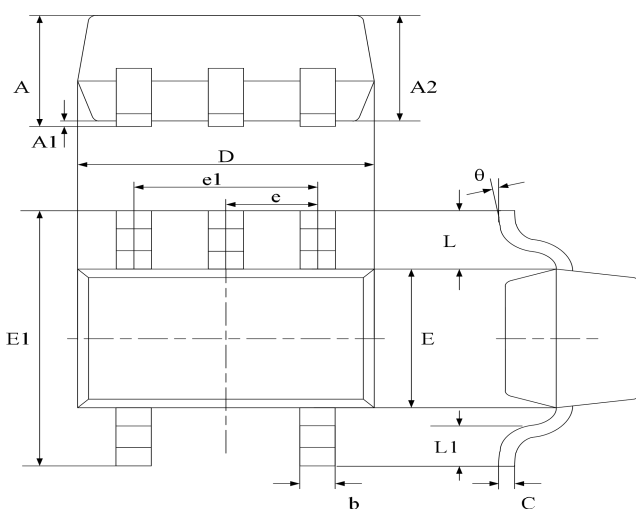
SOT23-6



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	—	—	1.25
A1	0	—	0.15
A2	1.00	1.10	1.20
A3	0.60	0.65	0.70
b	0.36	—	0.50
b1	0.36	0.38	0.45
c	0.14	—	0.20
c1	0.14	0.15	0.16
D	2.826	2.926	3.026
E	2.60	2.80	3.00
E1	1.526	1.626	1.726
e	0.90	0.95	1.00
e1	1.80	1.90	2.00
L	0.35	0.45	0.60
L1	0.59REF		
L2	0.25BSC		
R	0.10	—	—
R1	0.10	—	0.20
theta	0°	—	8°
theta 1	3°	5°	7°
theta 2	6°	—	14°

SC70-5 (SOT353)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.800	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.800	0.900	0.035	0.039
b	0.150	0.350	0.006	0.014
C	0.080	0.150	0.003	0.006
D	1.8500	2.150	0.079	0.087
E	1.100	1.400	0.045	0.053
E1	1.950	2.200	0.085	0.096
e	0.850 typ.		0.026 typ.	
e1	1.200	1.400	0.047	0.055
L	0.42 ref.		0.021 ref.	
L1	0.260	0.460	0.010	0.018
$\theta$	0°	8°	0°	8°

Ordering information

Order code	Package	Baseqty	Deliverymode	Marking
UMW TSV6391ICT	SC70-5	3000	Tape and reel	K41 U
UMW TSV6391AICT	SC70-5	3000	Tape and reel	K20 U
UMW TSV6390ILT	SOT23-6	3000	Tape and reel	K19 U
UMW TSV6390AILT	SOT23-6	3000	Tape and reel	K42 U